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Nota di contenuto	Polar modulation and bipolar RF power devices,"E. -- A fully integrated 24 GHz fractional PLL with a low-power synchronized ring oscillator divider,"O. -- A 40GHz superheterodyne receiver integrated in 0.13/spl mu/m BiCMOS SiGe:C HBT technology,"S. -- A fully integrated 60 GHz LNA in SiGe:C BiCMOS technology,"Y. -- A 10 /spl mu/m thick RF-ID tag for chip-in-paper applications,"R. -- Offset voltage of Schottky-collector silicon-on-glass vertical PNP's,"G. -- Thin film magnetic materials for RFIC passives,"Y. -- Usage of HBTs beyond BV/sub CEO/,"J. -- Unified electro-thermal stability criterion for bipolar transistors,"T. -- Assessing reliability issues in cryogenically-operated SiGe HBTs,"Chendong -- Electrothermal stability of bipolar transistors at medium- and high-current operation regimes,"N. -- The effects of layout variation on the thermal characteristics of SiGe HBTs,"J. -- Statistical modeling of high-frequency bipolar transistors,"M. -- Study of bipolar transistor matching at high current level with various test configurations leading to a new model approach,"S. -- Improved vertical PNP collector-base breakdown using 2D Monte-Carlo TCAD simulations,"A. -- BSCR ESD protection in 250V process taking into account the turn-off effect,"V. -- New lateral DMOS and IGBT structures realized on a partial SOI substrate based on LEGO process,"I. -- High-voltage semiconductor devices: status and trends,"G. -- A 43-45Gb/s 2.5V integrated clock and data recovery circuit in SiGe using low-voltage topologies,"D. -- NOR/OR register based ECL circuits for maximum data rate,"H. -- A 10Gb/s injection-locked clock recovery

circuit in 47GHz f/sub T/ SiGe BiCMOS,"Jing-Hong -- Notice of Violation of IEEE Publication Principles: A 12.5Gb/s electro-absorption-modulator driver using a cascode switch with dynamic biasing and adaptive RC compensation,"A. -- High dynamic range, high efficiency power amplifiers for wireless communications,"P. -- Improved hybrid SiGe HBT class-AB power amplifier efficiency using varactor-based tunable matching networks,"W. -- Experimental procedure to optimize out-of-band terminations for highly linear and power efficient bipolar class-AB RF amplifiers,"M. -- A VSWR-rugged silicon bipolar RF power amplifier,"A. -- 300 GHz f/sub max/ self-aligned SiGeC HBT optimized towards CMOS compatibility,"P. -- Ultra-low base resistance self-aligned SEG SiGe HBTs for high-sensitivity wide-bandwidth amplifiers,"T. -- A self-aligned vertical HBT for thin SOI SiGeC BiCMOS,"G. -- A low-cost SiGe:C BiCMOS technology with embedded flash memory and complementary LDMOS module,"D. -- High performance, low complexity vertical PNP BJT integrated in a 0.18/ μm SiGe BiCMOS technology,"B. -- A 100dB+ SFDR 80MSPS 14 bit 0.35/ μm BiCMOS pipeline ADC,"S. -- A 7-bit, 18 GHz SiGe HBT comparator for medium resolution A/D conversion,"Xiangtao -- An 8-bit, 12 GSAMPLE/sec SiGe track-and-hold amplifier,"Yuan -- A 12 GHz SiGe BiCMOS limiting amplifier with wide dynamic range peak detect circuitry for use in 10GBit optical systems,"R. -- Resonance phase operation of heterobipolar transistors beyond their transit frequency,"E. -- Next generation pixel scaling for the digital micromirror device,"J. -- Silicon based system-in-package: a passive integration technology combined with advanced packaging and system based design tools to allow a breakthrough in miniaturization,"F. -- IC/microfluidic hybrid system for biology: review,"Yong -- Input non-quasi-static effect in SiGe HBTs and its impact on noise modeling,"Kejun -- A transit time model for thin SOI Si/SiGe HBT,"S. -- An extended two-port method for the determination of the base and emitter resistance,"Z. -- The impact of low-frequency noise variations on the modeling and operation of SiGe circuits,"Zhenrong -- Silicon-germanium ICs for satellite microwave front-ends,"C. -- 20 GHz bipolar RF RMS power detectors,"Tao -- A 24 GHz broadband SiGe HBT limiting amplifier,"R. -- Experimental comparison of $I_{\text{sub } c}/V_{\text{sub } ce}$ parameters and large-signal performance for III-V HBTs,"C. -- On the optimization of lateral pnp BJTs found in BiCMOS process technologies,"E. -- Impact of burn-in effect and base strain on low frequency noise in InGaAsN HBTs,"Hua -- Identification and analysis of a new BJT parametric mismatch phenomenon,"N. -- A low-voltage feedforward-linearized broadband mixer,"S. -- Characteristics of SiGe device fabricated by SiGe BiCMOS technology and its application to a 5.8 GHz MMIC down-conversion mixer,"Sang-Heung -- Resonant-inductive degeneration for a fourfold phase-noise improvement of a 5.7GHz-band VCO,"A. -- A low-phase noise 5-GHz CCNF Colpitts VCO with parallel-branch inductors,"Ja-Yol -- A BiCMOS upconverter with 1.9 GHz multiband frequency synthesizer for DVB-RCT application,"E. -- Using SiGe HBT technology for extreme environment electronics,"J. -- 2-D analysis of device parasitics for 800/1000 GHz f/sub T/f/sub max/ SiGe HBT,"Yun -- Substrate bias effects in vertical SiGe HBTs fabricated on CMOS-compatible thin film SOI,"Tianhing -- Investigation of technology scaling effect on SiGe HBT oscillator phase noise using impulse sensitivity function,"Jin -- On the delay times in vertically scaled SiGe HBTs,"P. -- SiGe profile optimization for low noise using microscopic noise simulation,"Yan -- QUBiC4plus: a cost-effective BiCMOS manufacturing technology with elite passive enhancements optimized for 'silicon-based' RF-system-in-package environment,"P. -- Impact of

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